



S E M I C O N D U C T O R

BZV85/C 2V7 THRU BZV85/C 200

1W SILICON PLANAR ZENER DIODES

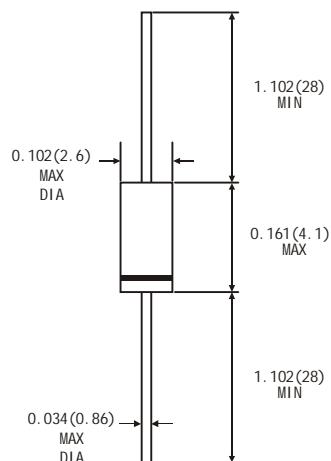
FEATURES

- For use in stabilizing and clipping circuits with high power rating.
- The Zener voltage are graded according to the international E24 standard.
- Other voltage tolerance and higher Zener voltage on request.

MECHANICAL DATA

- Case: DO-41 glass case
- Weight: Approx. 0.35 gram

DO-41(GLASS)



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES) ($T_A=25\text{ C}$) °

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at $T_A=25^\circ\text{C}$	P_{tot}	1 ¹⁾	W
Junction temperature	T_J	200	$^\circ\text{C}$
Storage temperature range	T_{STG}	-65 to +200	$^\circ\text{C}$

1) Valid provided that a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS ($T_A=25\text{ C}$)

	Symbols	Min	Typ	Max	Units
Thermal resistance junction to ambient air	R_{thA}			170 ¹⁾	K/W
Forward voltage at $I_F=200\text{mA}$	V_F			1.2	V

1) Valid provided that a distance of 8mm from case are kept at ambient temperature

BZX55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage range ¹⁾			Dynamic resistance			Reverse leakage current		Temp Coefficient of zener voltage		
	V _{ZNOM}	I _{ZT} for V _{ZT} ²⁾		r _{ZP} and r _{ZK} at I _{ZT}			I _R ²⁾ at V _R				
		V	mA	V	Ω	Ω	mA	μA	V	%/K	
BZV 85/C 2 V 7	2.7	80	2.5...2.9	<20	<400	1	<150	1	-0.08...-0.05		
BZX 85/C 3 V 0	3.0		2.8...3.2				<100				
BZX 85/C 3 V 3	3.3	70	3.1...3.5	<15	<500		<40				
BZX 85/C 3 V 6	3.6	60	3.4...3.8				<20				
BZX 85/C 3 V 9	3.9		3.7...4.1				<10				
BZX 85/C 4 V 3	4.3	50	4.0...4.6	<13	<600		<3	<1	-0.07...+0.01		
BZX 85/C 4 V 7	4.7	45	4.4...5.0				1.5				
BZX 85/C 5 V 1	5.1		4.8...5.4	<10	<500		2				
BZX 85/C 5 V 6	5.6	35	5.2...6.0	<7	<400		3				
BZX 85/C 6 V 2	6.2		5.8...6.6	<4	<300	0.5	4				
BZX 85/C 6 V 8	6.8		6.4...7.2	<3.5			4.5				
BZX 85/C 7 V 5	7.5		7.0...7.9	<3			6.2				
BZX 85/C 8 V 2	8.2	25	7.7...8.7	<5	<200		6.8				
BZX 85/C 9 V 1	9.1		8.5...9.6				7				
BZX 85/C 10	10		9.4...10.6				8.2				
BZX 85/C 11	11	20	10.4...11.6	<8	<300	<0.5	9.1				
BZX 85/C 12	12		11.4...12.7	<9	<350		10				
BZX 85/C 13	13		12.4...14.1	<10	<400		11	0.055...0.09	0.055...0.09		
BZX 85/C 15	15	15	13.8...15.6	<15	<500		12				
BZX 85/C 16	16		15.3...17.1				13	0.06...0.09	0.06...0.09		
BZX 85/C 18	18		16.8...19.1				15				
BZX 85/C 20	20	10	18.8...21.2	<24	<600	0.25	16	0.06...0.095	0.06...0.095		
BZX 85/C 22	22		20.8...23.3	<25			18				
BZX 85/C 24	24		22.8...25.6				20				
BZX 85/C 27	27	8	25.1...28.9	<30	<750		22				
BZX 85/C 30	30		28...32		<1000		24				
BZX 85/C 33	33		31...35	<35			27				
BZX 85/C 36	36		34...38	<40							

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Type	Zener Voltage range ¹⁾			Dynamic resistance			Reverse leakage current		Temp Coefficient of zener voltage		
	V _{ZNOM}	I _{ZT} for V _{ZT} ²⁾		r _Z and r _K at I _{ZK}			I _R ²⁾ at V _R				
	V	mA	V	Ω	Ω	mA	μA	V	%/K		
BZV 85/C 39	39	6	37...41	<50	<1000	0.25	<0.5	30	0.06...0.095		
BZX 85/C 43	43		40...46					33			
BZX 85/C 47	47		44...50					36			
BZX 85/C 51	51		48...54	<90	<115			39			
BZX 85/C 56	56	4	52...60					43			
BZX 85/C 62	62		58...66					47			
BZX 85/C 68	68		64...72	<125	<2000			51			
BZX 85/C 75	75		70...79					56			
BZX 85/C 82	82	2.7	77...87	<200	<3000			62	0.07...0.10		
BZX 85/C 91	91		85...96					68			
BZX 85/C 100	100		94...106					75			
BZX 85/C 110	110		104...116	<450	<4000			82			
BZX 85/C 120	120	2	114...127	<550	<4500			91	0.07...0.11		
BZX 85/C 130	130		124...141	<700	<5000			100			
BZX 85/C 150	150		138...156	<1000	<6000			110			
BZX 85/C 160	160	1.5	153...171	<1100	<6500			120			
BZX 85/C 180	180		168...191	<1200	<7000			130			
BZX 85/C 200	200		188...212	<1500	<8000			150			

Note 1) Tested with pulse t_p=20ms

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

SILICON PLANAR POWER ZENER DIODES

Admissible power dissipation versus ambient temperature
(Valid provided that leads at a distance of 10mm from case
are kept at ambient temperature)

